

WHAT IS CLAIMED IS:

1. An electro-optical device comprising, above a substrate:  
data lines extending in a first direction;  
scanning lines extending in a second direction and intersecting the data lines;  
pixel electrodes and thin film transistors disposed so as to correspond to intersection regions of the data lines and the scanning lines;  
storage capacitors electrically connected to the thin film transistors and the pixel electrodes; and  
shielding layers disposed between the data lines and the pixel electrodes, nitride films being included in the shielding layers and are formed along the data lines and being wider than the data lines.
2. The electro-optical device according to Claim 1, a planarization process being performed on the surfaces of interlayer insulating films arranged as the bases of the pixel electrodes.
3. The electro-optical device according to Claim 1, each of the data lines being formed of the same film as one of a pair of electrodes which constitute each of the storage capacitors.
4. The electro-optical device according to Claim 3, the data lines forming a laminated structure of an aluminum film and a conductive polysilicon film.
5. The electro-optical device according to Claim 1, further comprising:  
relay layers being electrically connected to the pixel electrodes and one of a pair of electrodes which constitute each of the storage capacitors.
6. The electro-optical device according to Claim 5, the relay layers being made of aluminum films and nitride films.
7. The electro-optical device according to Claim 5, the shielding layers being formed of the same films as the relay layers.
8. The electro-optical device according to Claim 1, the nitride films being formed on the surfaces of the data lines.
9. An electro-optical device comprising, above a substrate:  
data lines extending in a first direction;  
scanning lines extending in a second direction and intersecting the data lines;  
pixel electrodes and thin film transistors disposed so as to correspond to intersection regions of the data lines and the scanning lines;

storage capacitors electrically connected to the thin film transistors and the pixel electrodes; and

shielding layers disposed between the data lines and the pixel electrodes, nitride films being included in the data lines.

10. The electro-optical device according to Claim 9, the nitride films being formed in regions where the scanning lines extend.

11. The electro-optical device according to Claim 9, the nitride films being formed around image display regions defined as regions where the pixel electrodes, the data lines, and the scanning lines are formed.

12. The electro-optical device according to Claim 9, the nitride films formed on the data lines being wider than the data lines.

13. The electro-optical device according to Claim 12, each of the edges of the nitride films being larger than each of the edges of the data lines by 0.1 to 2.2  $\mu\text{m}$ .

14. The electro-optical device according to Claim 9, the thickness of the nitride films being 10 to 100 nm.

15. The electro-optical device according to Claim 9, further comprising:  
another substrate that faces the substrate with an electro-optical material interposed therebetween and light-shielding films formed on the other substrate so as to correspond to the scanning lines and the data lines,  
the nitride films being narrower than the light-shielding films.

16. The electro-optical device according to Claim 15, each of the edges of the nitride films being smaller than each of the edges of the light-shielding films by up to 1  $\mu\text{m}$ .

17. The electro-optical device according to Claim 9, further comprising:  
another substrate that faces the substrate with an electro-optical material interposed therebetween and light-shielding films formed on the other substrate so as to correspond to the scanning lines and the data lines,  
the nitride films being wider than the light-shielding films.

18. The electro-optical device according to Claim 1, the shielding layers being formed of a transparent conductive material and are formed over the entire surface of the substrate.

19. The electro-optical device according to Claim 9, the shielding layers being formed of a transparent conductive material and being formed over the entire surface of the substrate in a mat shape.

20. An electro-optical device comprising, above a substrate:  
 data lines extending in a first direction;  
 scanning lines extending in a second direction and intersecting the data lines;  
 pixel electrodes and thin film transistors disposed so as to correspond to  
 intersection regions of the data lines and the scanning lines;  
 storage capacitors electrically connected to the thin film transistors and the  
 pixel electrodes; and  
 shielding layers disposed between the data lines and the pixel electrodes,  
 dielectric films which constitute the storage capacitors being made of a  
 plurality of layers including different materials and one of the plurality of the layers being  
 made of a material having a higher dielectric constant than those of the other layers, and  
 nitride films being included in the data lines.
21. An electronic apparatus having an electro-optical device comprising, above a  
 substrate:  
 data lines extending in a first direction;  
 scanning lines extending in a second direction and intersecting the data lines;  
 pixel electrodes and thin film transistors disposed so as to correspond to  
 intersection regions of the data lines and the scanning lines;  
 storage capacitors electrically connected to the thin film transistors and the  
 pixel electrodes; and  
 shielding layers disposed between the data lines and the pixel electrodes,  
 nitride films being included in the shielding layers and are formed along the  
 data lines and wider than the data lines.